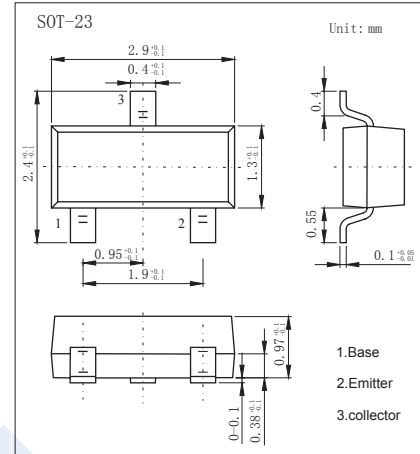


## NPN Transistors

## BFS17 (KFS17)

## ■ Features

- Collector Current Capability  $I_c=25\text{mA}$
- Collector Emitter Voltage  $V_{CE0}=15\text{V}$

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	25	V
Collector - Emitter Voltage	$V_{CE0}$	15	
Emitter - Base Voltage	$V_{EB0}$	2.5	
Collector Current - Continuous	$I_c$	25	mA
Collector Current - Pulse	$I_{CP}$	50	
Collector Power Dissipation	$P_c$	300	mW
Thermal Resistance From Junction to Soldering Point	$R_{\theta JS}$	260	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_c = 100 \mu\text{A}, I_E = 0$	25			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_c = 1 \text{mA}, I_B = 0$	15			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 100 \mu\text{A}, I_c = 0$	2.5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = 25 \text{V}, I_E = 0$			100	nA
Emitter cut-off current	$I_{EB0}$	$V_{EB} = 2.5 \text{V}, I_c = 0$			100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 25 \text{mA}, I_B = 2.5 \text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 25 \text{mA}, I_B = 2.5 \text{mA}$			1.2	
DC current gain	$h_{FE}$	$V_{CE} = 1 \text{V}, I_c = 2 \text{mA}$	25	90		
		$V_{CE} = 1 \text{V}, I_c = 25 \text{mA}$	25	90		
Collector Capacitance	$C_c$	$V_{CB} = 10 \text{V}, I_E = I_c = 0, f = 1 \text{MHz}$			1.5	pF
Emitter Capacitance	$C_e$	$V_{EB} = 0.5 \text{V}, I_c = I_c = 0, f = 1 \text{MHz}$			2	
Feedback Capacitance	$C_{re}$	$V_{CE} = 5 \text{V}, I_c = 1 \text{mA}, f = 1 \text{MHz}$		0.65		
Noise Figure	NF	$V_{CE} = 5 \text{V}, I_c = 2 \text{mA}, R_s = 50 \Omega, f = 500 \text{MHz}$		4.5		dB
Transition frequency	$f_t$	$V_{CE} = 5 \text{V}, I_c = 2 \text{mA}, f = 500 \text{MHz}$		1		GHz
		$V_{CE} = 5 \text{V}, I_c = 25 \text{mA}, f = 500 \text{MHz}$		1.6		

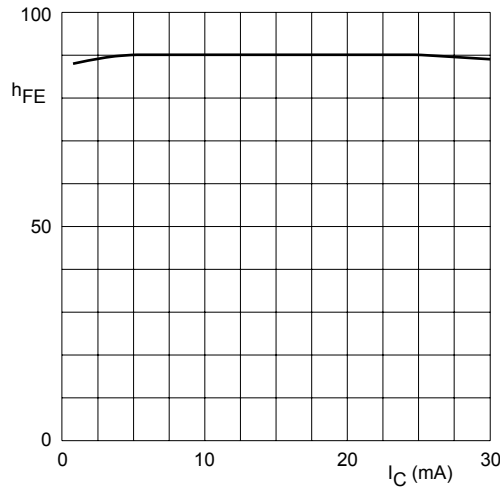
## ■ Marking

Marking	E1*
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## NPN Transistors

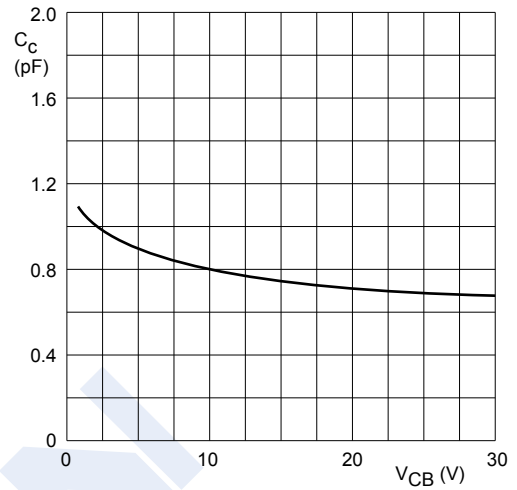
### BFS17 (KFS17)

■ Typical Characteristics



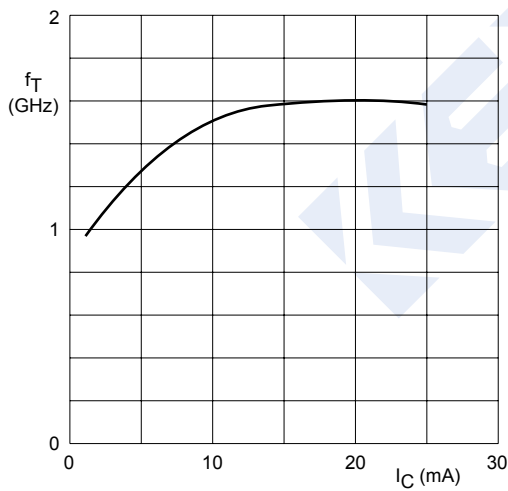
$V_{CE} = 1\text{ V}; T_j = 25\text{ }^\circ\text{C}.$

Fig.2 DC current gain as a function of collector current.



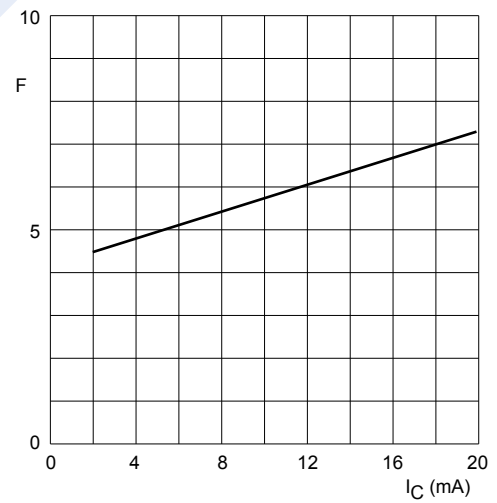
$I_E = I_B = 0; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}.$

Fig.3 Collector capacitance as a function of collector-base voltage.



$V_{CE} = 5\text{ V}; f = 500\text{ MHz}; T_j = 25\text{ }^\circ\text{C}.$

Fig.4 Transition frequency as a function of collector current.



$V_{CE} = 5\text{ V}; R_S = 50\ \Omega; f = 500\text{ MHz}; T_j = 25\text{ }^\circ\text{C}.$

Fig.5 Minimum noise figure as a function of collector current.